

UNITED STATES PATENT AND TRADEMARK OFFICE

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

| APPLICATION NO. | FILING DATE | FIRST NAMED INVENTOR | ATTORNEY DOCKET NO. | CONFIRMATION NO. |
|--|-----------------|----------------------|------------------------|------------------|
| 09/653,281 | 08/31/2000 | Kevin L. Beaman | M4065.0278/P27899-0818 | 4745 |
| 7 | 7590 05/25/2004 | | EXAMINER | |
| Thomas J D'Amico | | | BOOTH, RICHARD A | |
| Dickstein Shapiro Morin & Oshinsky LLP | | | - | |
| 2101 L Street NW | | | ART UNIT | PAPER NUMBER |
| Washington, DC 20037-1526 | | | 2812 | |

DATE MAILED: 05/25/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

| | | AL | |
|--|---|---|-------|
| | Application No. | Applicant(s) | |
| Office Action Occurs | 09/653,281 | BEAMAN ET AL. | |
| Office Action Summary | Examiner | Art Unit | |
| | Richard A. Booth | 2812 | ····· |
| The MAILING DATE of this communication a Period for Reply | ppears on the cover sheet | with the correspondence address | |
| A SHORTENED STATUTORY PERIOD FOR REF THE MAILING DATE OF THIS COMMUNICATION - Extensions of time may be available under the provisions of 37 CFR after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a - If NO period for reply is specified above, the maximum statutory perion - Failure to reply within the set or extended period for reply will, by state Any reply received by the Office later than three months after the may earned patent term adjustment. See 37 CFR 1.704(b). | N. 1.136(a). In no event, however, may reply within the statutory minimum of t od will apply and will expire SIX (6) Me tute, cause the application to become | a reply be timely filed nirty (30) days will be considered timely. DNTHS from the mailing date of this communication. ABANDONED (35 U.S.C. § 133). | |
| Status | | | |
| 1) Responsive to communication(s) filed on 19 | April 2004. | | |
| | his action is non-final. | | |
| 3) Since this application is in condition for allow closed in accordance with the practice unde | | | |
| | i Ex parto waayie, 1900 O | .5. 11, 700 5.0. 210. | |
| Disposition of Claims | ***/**** | · atia | |
| 4) Claim(s) 1-3,6-14,16,18,21-29,31 and 35-45 | | ication. | |
| 4a) Of the above claim(s) is/are withd 5) Claim(s) is/are allowed. | nawn nom consideratioff. | | |
| 5) | 5 is/are rejected. | | |
| 7) Claim(s) is/are objected to. | | | |
| 8) Claim(s) are subject to restriction and | d/or election requirement. | | |
| Application Papers | | | |
| 9) ☐ The specification is objected to by the Exam | iner. | | |
| 10) The drawing(s) filed on is/are: a) a | | o by the Examiner. | |
| Applicant may not request that any objection to t | he drawing(s) be held in abey | ance. See 37 CFR 1.85(a). | |
| Replacement drawing sheet(s) including the corr | | | |
| 11) The oath or declaration is objected to by the | Examiner. Note the attach | ed Office Action or form PTO-152. | |
| Priority under 35 U.S.C. § 119 | | | |
| 12) Acknowledgment is made of a claim for fore | ign priority under 35 U.S.C | . § 119(a)-(d) or (f). | |
| a) ☐ All b) ☐ Some * c) ☐ None of: | | ę | |
| 1. Certified copies of the priority docume | | | |
| 2. Certified copies of the priority docume | | | |
| 3. Copies of the certified copies of the p | | en received in this National Stage | |
| application from the International Bur * See the attached detailed Office action for a | | of received. | |
| See the attached detailed Office action for a | not of the octahed copies in | oc 1000110d. | |
| | | | |
| Attachment(s) 1) Notice of References Cited (PTO-892) | 4) Tintervie | w Summary (PTO-413) | |
| Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948) | Paper N | lo(s)/Mail Date | |
| 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/Paper No(s)/Mail Date | (08) 5) ☐ Notice (6) ☐ Other: _ | of Informal Patent Application (PTO-152) | |
| S. Patent and Trademark Office | -, | D. (D. V. 0.15 (0.55) | 4 |

Application/Control Number: 09/653,281

Art Unit: 2812

DETAILED ACTION

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1-3, 6-16, 18, 21-31, and 34-45 are rejected under 35 U.S.C. 103(a) as being unpatentable over Wang et al., U.S. Patent 6,376,309 in view of Hoff et al., "Atomic Oxygen and the thermal oxidation of silicon" or Ruzyllo et al., "Evaluation of Thin Oxides Grown by the Atomic Oxygen Afterglow Method".

Wang et al. shows the invention as claimed including forming a tunnel oxide 404 on a substrate 402; forming a first conductor 406 over the tunnel oxide 404; forming an insulating layer 410 over the first conductor layer, the insulating layer comprising a first oxide layer over the first conductor layer, a nitride layer over the first oxide layer, and a second oxide layer over the nitride layer, wherein the second oxide layer is formed by oxidizing said nitride layer to a thickness of fifty angstroms (see column 3, lines 39-54); forming a second conductor layer 412 over the insulating layer; etching at least the first conductor layer, the second conductor layer, and the insulating layer, thereby defining at least one stacked structure (see Figure 3).

Note with regard to claims 6, 21, and 36, the hydrogen and oxygen present when forming the second oxide layer will react to form steam.

Wang et al. fails to show forming the second oxide layer using an oxidizing ambient in atomic oxygen to form the oxide layer with a thickness of 60% of a targeted thickness and at various temperatures and times.

Both Hoff et al., "Atomic Oxygen and the thermal oxidation of silicon" and Ruzyllo et al., "Evaluation of Thin Oxides Grown by the Atomic Oxygen Afterglow Method" disclose forming an oxide layer in a microwave environment using an oxidizing method with atomic oxygen (see abstracts of both methods). In view of this disclosure, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the process of Wang et al. so as to form the second oxide layer using the process taught by Hoff et al. or Ruzyllo et al. because both of these processes allow for oxide growth at low temperatures with high breakdown values.

With respect to the particular time and temperature of the oxidation, it would have been obvious to determine through routine experimentation the optimum time and temperature to conduct the oxidation process based upon a variety of factors including the desired thermal budget and would not lend patentability to the instant application absent the showing of unexpected results.

Response to Arguments

Applicant's arguments filed 4/19/04 have been fully considered but they are not persuasive. Regarding applicant's argument that Wang fails to show the particular processing parameters of the atomic oxidation, one cannot show nonobviousness by attacking references individually where the rejections are based on combinations of

Application/Control Number: 09/653,281

Art Unit: 2812

references. See *In re Keller*, 642 F.2d 413, 208 USPQ 871 (CCPA 1981); *In re Merck* & Co., 800 F.2d 1091, 231 USPQ 375 (Fed. Cir. 1986). Furthermore, the secondary references relied upon in the above rejection under 35 USC are used to show the atomic oxidation process.

Conclusion

THIS ACTION IS MADE FINAL. Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Richard A. Booth whose telephone number is (571) 272-1668. The examiner can normally be reached on Monday-Thursday from 7:30-6:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, John Niebling can be reached on (571) 272-1679. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Application/Control Number: 09/653,281

Art Unit: 2812

Page 5

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Richard & Booth Primary Examiner Art Unit 2812

May 19, 2004